

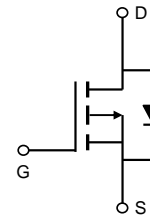
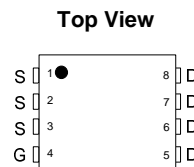
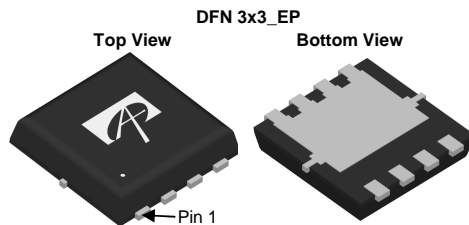
General Description

The AON7407 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

Product Summary

V_{DS}	-20V
I_D (at $V_{GS}=-4.5V$)	-40A
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	< 9.5m Ω
$R_{DS(ON)}$ (at $V_{GS}=-2.5V$)	< 12.5m Ω
$R_{DS(ON)}$ (at $V_{GS}=-1.8V$)	< 18m Ω

100% UIS Tested
 100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current ^G	I_D	$T_C=25^\circ\text{C}$	-40
		$T_C=100^\circ\text{C}$	-29
Pulsed Drain Current ^C	I_{DM}	-100	A
Continuous Drain Current	I_{DSM}	$T_A=25^\circ\text{C}$	-14.5
		$T_A=70^\circ\text{C}$	-11.5
Avalanche Current ^C	I_{AS}, I_{AR}	-40	A
Avalanche energy $L=0.1\text{mH}$ ^C	E_{AS}, E_{AR}	80	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	29
		$T_C=100^\circ\text{C}$	12
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ\text{C}$	3.1
		$T_A=70^\circ\text{C}$	2
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	30	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A,D}				
Maximum Junction-to-Case	$R_{\theta JC}$	3.5	4.2	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±8V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.3	-0.55	-0.9	V
I _{D(ON)}	On state drain current	V _{GS} =-4.5V, V _{DS} =-5V	-100			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V, I _D =-14A T _J =125°C		7.6	9.5	mΩ
		V _{GS} =-2.5V, I _D =-13A		9.3	12.5	
		V _{GS} =-1.8V, I _D =-11A		11.4	18	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-14A		72		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.52	-1	V
I _S	Maximum Body-Diode Continuous Current				-35	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-10V, f=1MHz	2795	3495	4195	pF
C _{oss}	Output Capacitance		365	528	690	pF
C _{riss}	Reverse Transfer Capacitance		255	425	595	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		2.8	5.6	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =-4.5V, V _{DS} =-10V, I _D =-14A	35	44	53	nC
Q _{gs}	Gate Source Charge		9			nC
Q _{gd}	Gate Drain Charge		11			nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-4.5V, V _{DS} =-10V, R _L =0.75Ω, R _{GEN} =3Ω		18		ns
t _r	Turn-On Rise Time			32		ns
t _{D(off)}	Turn-Off DelayTime			136		ns
t _f	Turn-Off Fall Time			59		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-14A, dI/dt=500A/μs	26	33	40	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-14A, dI/dt=500A/μs	80	100	120	nC

- A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on R_{θJA} t ≤ 10s value and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- B. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J ≈ 25°C.
- D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating.
- G. The maximum current rating is package limited.
- H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

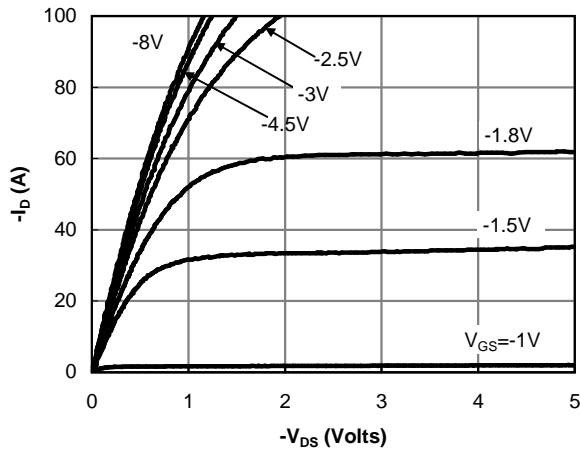


Fig 1: On-Region Characteristics (Note E)

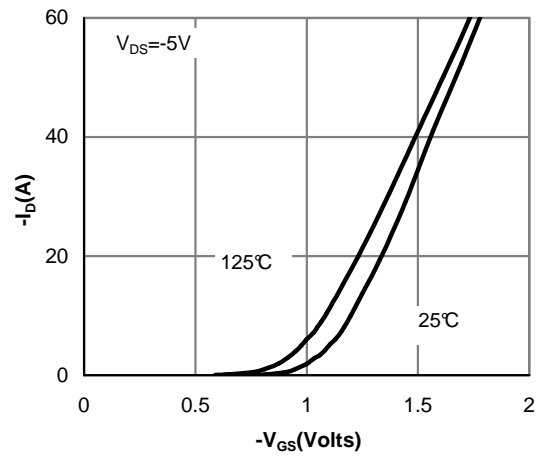


Figure 2: Transfer Characteristics (Note E)

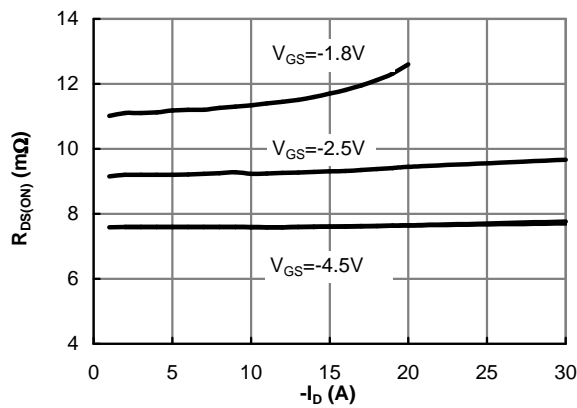


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

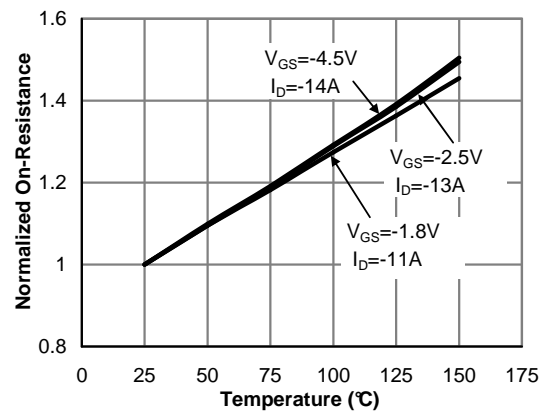


Figure 4: On-Resistance vs. Junction Temperature (Note E)

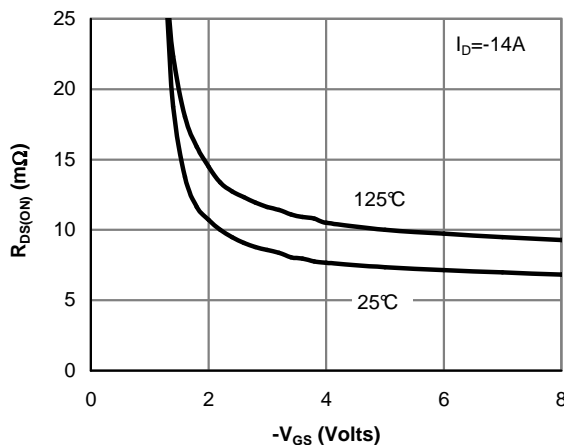


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

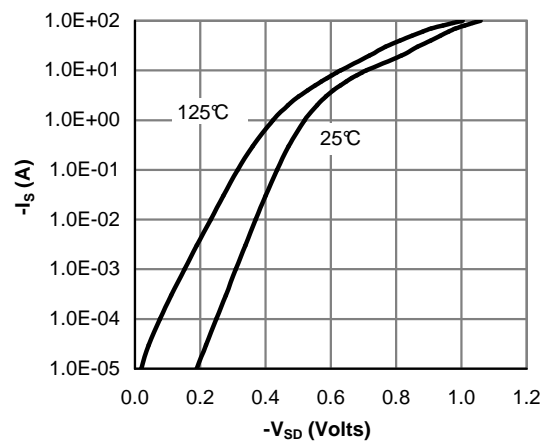


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

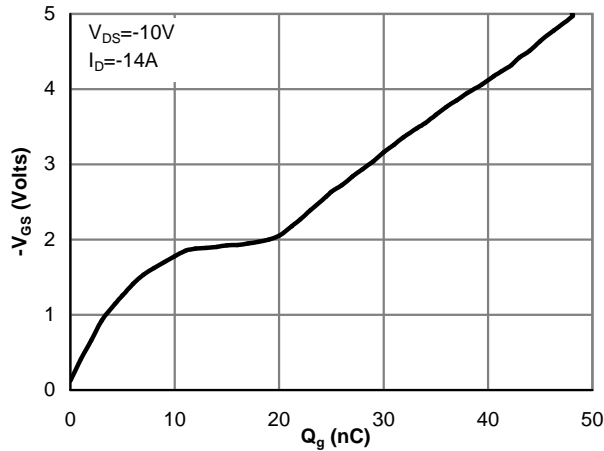


Figure 7: Gate-Charge Characteristics

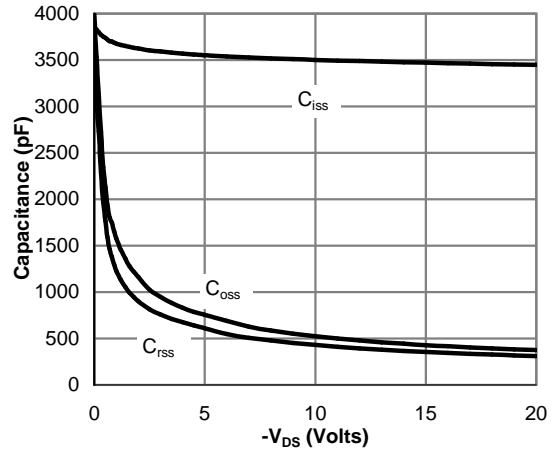


Figure 8: Capacitance Characteristics

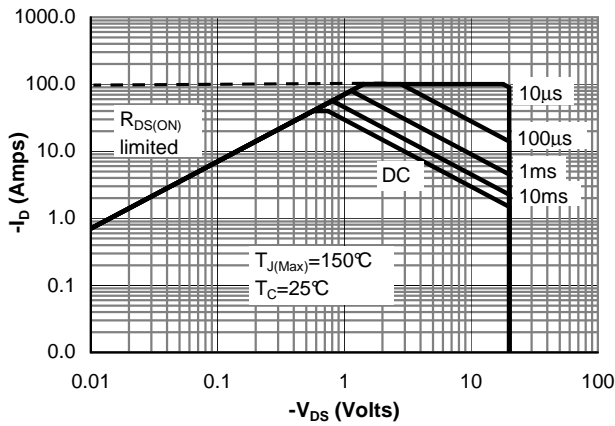


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

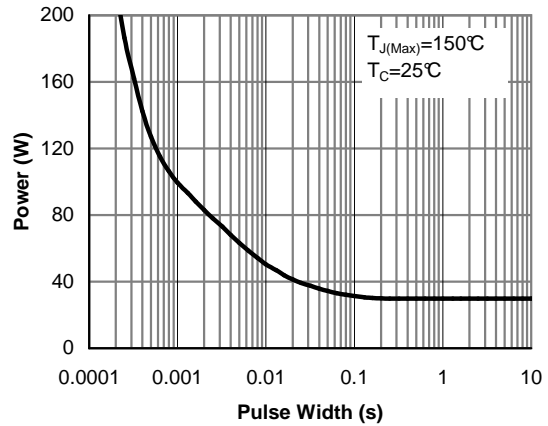


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

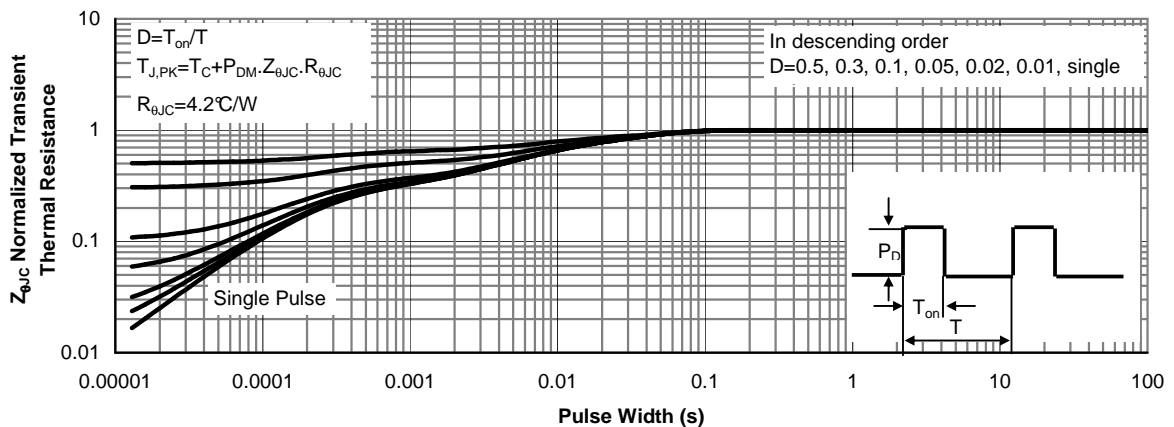


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

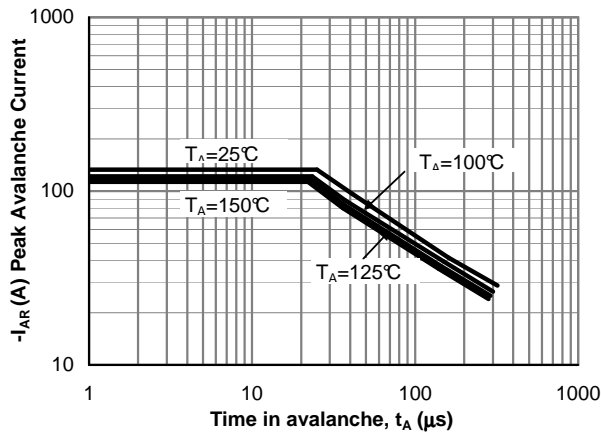


Figure 12: Single Pulse Avalanche capability (Note C)

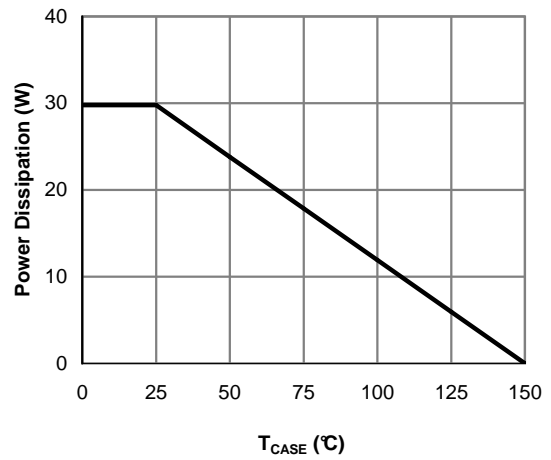


Figure 13: Power De-rating (Note F)

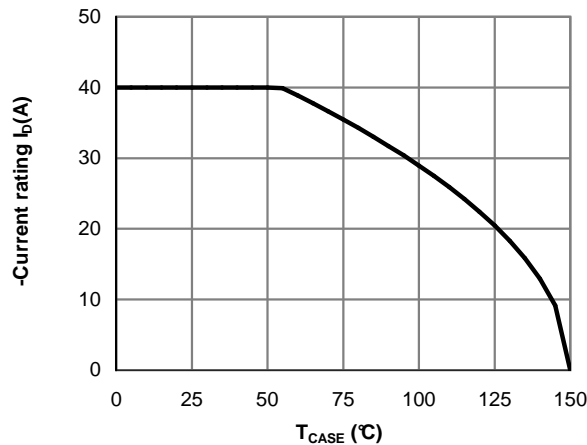


Figure 14: Current De-rating (Note E)

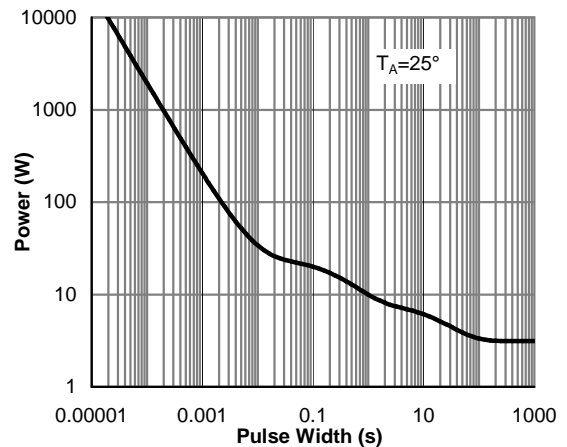


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

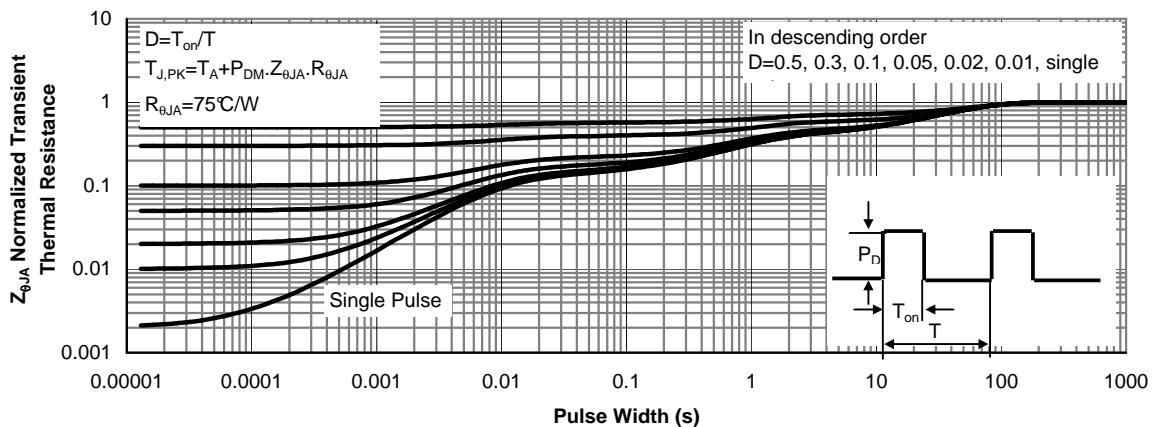
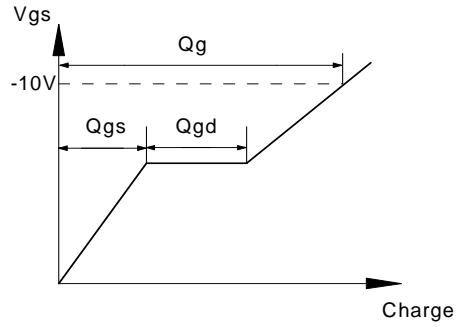
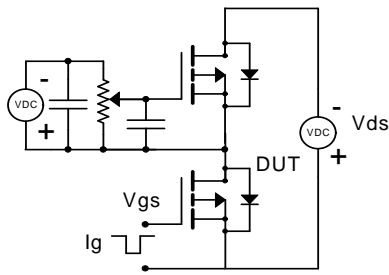
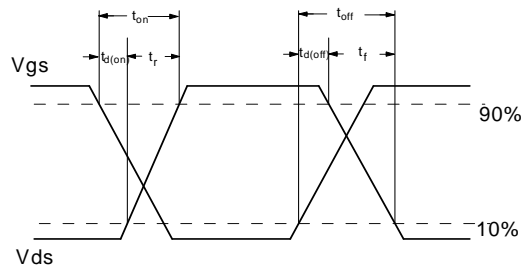
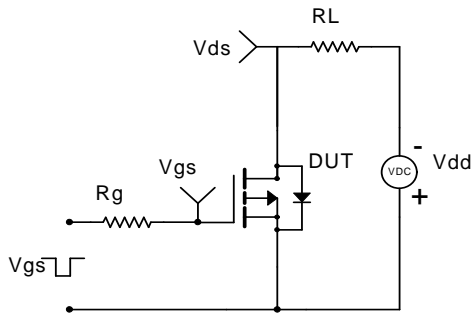


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

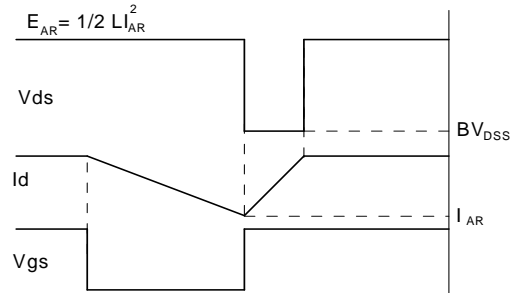
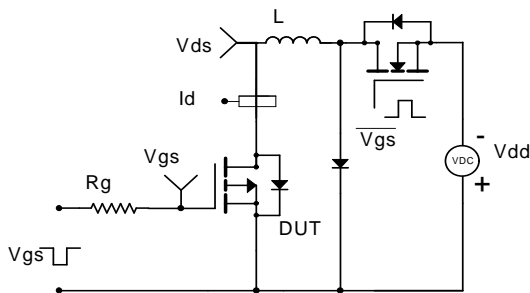
Gate Charge Test Circuit & Waveform



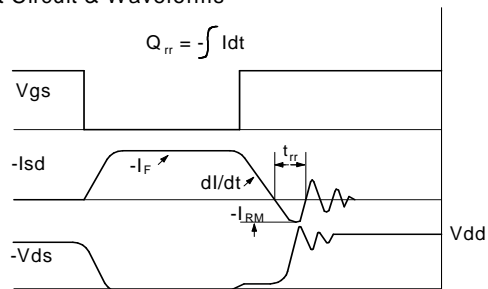
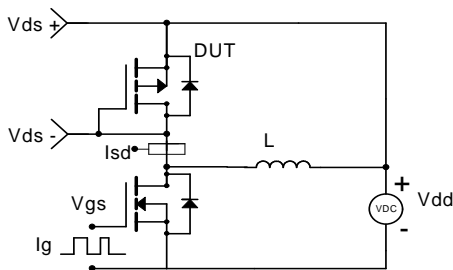
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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